

2SC1471
 TO3 Silicon NPN High Voltage Switching Transistor

SPECIFICATION

GENERAL DESCRIPTION:

ELECTRICAL CHARACTERISTICS – CARACTÉRISTIQUES ÉLECTRIQUES **

SYMBOLS	Min	Typ	Max	UNIT	TEST CONDITIONS – CONDITIONS DE MESURE
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OFF CHARACTERISTICS – CARACTÉRISTIQUES A L'ÉTAT BLOQUÉ

V_{CE0sus}	400			V	$I_B = 0, I_C = 0,2 A, L = 25 mH$
$V_{(BR)EBO}$	7		30	V	$I_C = 0, I_B = 0,1 A$
I_{CEX}			0,4 4	mA	$T_{case} = 25^{\circ}C$ $T_{case} = 125^{\circ}C$ $V_{CE} = V_{CEX}, V_{BE} = -2,5 V$
I_{CER}			1 8	mA	$T_{case} = 25^{\circ}C$ $T_{case} = 125^{\circ}C$ $V_{CE} = V_{CEX}, R_{BE} \leq 5 \Omega$
I_{EBO}			2	mA	$I_C = 0, V_{EB} = 5 V$

ON CHARACTERISTICS – CARACTÉRISTIQUES A L'ÉTAT CONDUCTEUR

V_{CEsat}^*			1,5	V	$I_C = 20 A, I_B = 4 A$ $I_C = 30 A, I_B = 8 A$
			1,5 5	V	$I_C = 16 A, I_B = 3,2 A$ $I_C = 24 A, I_B = 5 A$
V_{BEsat}^*			1,6	V	$I_C = 20 A, I_B = 4 A$ $I_C = 16 A, I_B = 3,2 A$

DYNAMIC CHARACTERISTICS – CARACTÉRISTIQUES DYNAMIQUES

f_T		5		MHz	$f = 1 MHz, I_C = 1 A, V_{CE} = 10 V$
C_{22b}		500		pF	$f = 1 MHz, V_{CE} = 10 V$

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